



#### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	$55m\Omega @ V_{GS} = 4.5V$	4.6A
200	$100m\Omega @ V_{GS} = 2.5V$	3.4A

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

### Applications

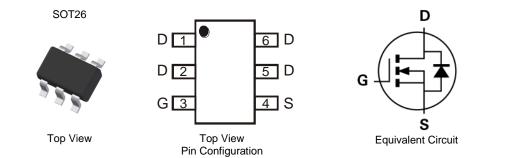
- DC-DC Converters
- Power Management Functions
- Backlighting

#### **Features and Benefits**

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (£3)
- Weight: 0.018 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMN2A03E6TA	SOT26	3,000/Tape & Reel
ZXMN2A03E6TC	SOT26	10,000/Tape & Reel

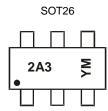
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



2A3 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage		V <sub>DSS</sub>	20	V	
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current, V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C \text{ (Note 6)}$ $T_A = +70^{\circ}C \text{ (Note 6)}$ $T_A = +25^{\circ}C \text{ (Note 5)}$	ID	4.6 3.7 3.7	A
Maximum Body Diode Forward Current (Note 6)			Is	2.7	А
Pulsed Drain Current (Note 7)		I <sub>DM</sub>	16	A	
Pulsed Source Current (Note 7)		I <sub>SM</sub>	16	А	

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 5)	PD	1.1 8.8	W mW/°C
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 6)	PD	1.7 13.6	W mW/°C
Thermal Resistance, Junction to Ambient	Steady State (Note 5)	Bass	113	°C/W
	Steady State (Note 6)	R <sub>0JA</sub>	70	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)	•					
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.7	_		V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance (Note 8)	Р		_	55	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7.2A
Static Drain-Source On-Resistance (Note 6)	R <sub>DS(ON)</sub>		—	100	11152	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4.6A
Diode Forward Voltage (Note 8)	V <sub>SD</sub>		0.85	0.95	V	$V_{GS} = 0V, I_S = 4.1A$
Forward Transconductance (Notes 8 & 10)	<b>g</b> fs		13	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 7.2A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C <sub>iss</sub>		837			
Output Capacitance	Coss	_	168	—	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	90	_		
Total Gate Charge	Qg		8.2	_		
Gate-Source Charge	Q <sub>gs</sub>		2.3	_	nC	$V_{DS} = 10V, I_D = 7.2A, V_{GS} = 4.5V$
Gate-Drain Charge	Q <sub>gd</sub>		2.0	_		
Turn-On Delay Time	t <sub>D(on)</sub>		4.7	_		
Turn-On Rise Time	tr		5.7	_	nS	$V_{GS} = 4.5V, V_{DD} = 10V, R_G = 6.0\Omega,$
Turn-Off Delay Time	t <sub>D(off)</sub>		18.5	_	15	I <sub>D</sub> = 1.0A
Turn-Off Fall Time	tf		10.5		1	
Body Diode Reverse Recovery Time	t <sub>rr</sub>		12	_	nS	1 1 0 0 dl/dt 100 0/00
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		4.9	_	nC	- I <sub>F</sub> = 1.9A, dI/dt = 100A/μs

Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For a device surface mounted on FR4 PCB measured at t  $\leq$ 5 secs.

7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

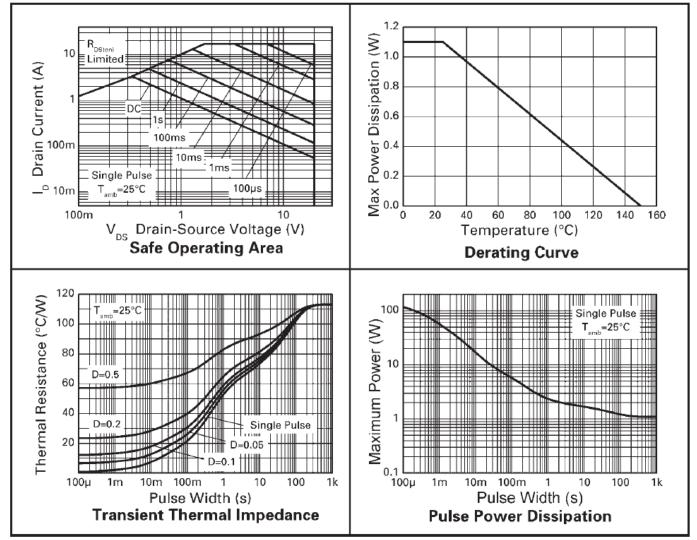
8. Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle  $\leq$  2%.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

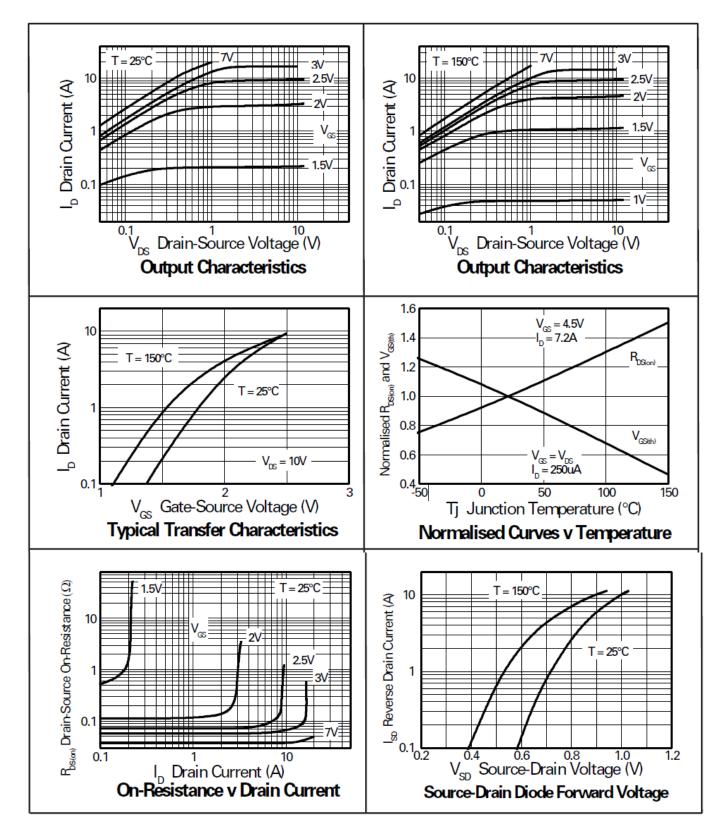


## **TYPICAL CHARACTERISTICS**





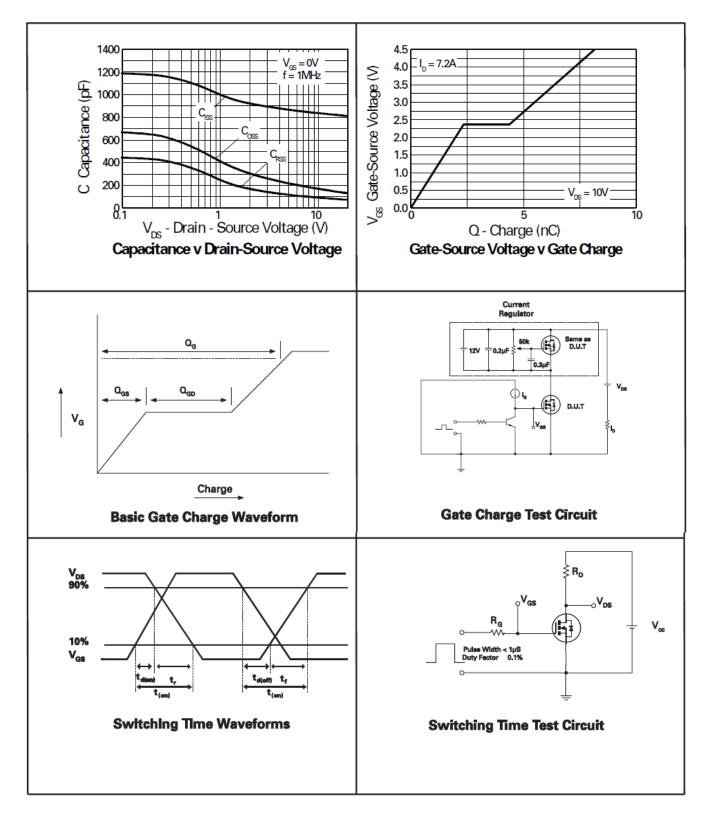
# **TYPICAL CHARACTERISTICS**





## ZXMN2A03E6

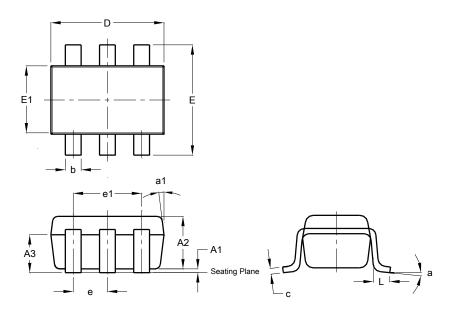
## **TYPICAL CHARACTERISTICS**





## **Package Outline Dimensions**

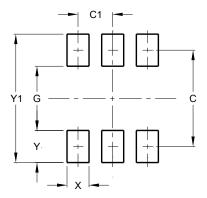
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
c	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
Е	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	All Dimensions in mm							

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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